

# SKCD 46 C 120 I4F



**CAL-DIODE**

$I_F = 75\text{ A}$

$V_{RRM} = 1200\text{ V}$

Size: 6,70 mm x 6,70 mm

## SKCD 46 C 120 I4F

### Features

- max. junction 175 °C
- very low forward voltage drop
- positive temperature coefficient
- extreme soft recovery

### Typical Applications\*

- freewheeling diode for IGBT

### Absolute Maximum Ratings

| Symbol      | Conditions                                                  | Values                | Unit |
|-------------|-------------------------------------------------------------|-----------------------|------|
| $V_{RRM}$   | $T_j = 25\text{ °C}$ , $I_R = 0.12\text{ mA}$               | 1200                  | V    |
| $I_{F(AV)}$ | $T_c = 80\text{ °C}$ , $T_j = 175\text{ °C}$ , $F_i = PI/2$ | 48                    | A    |
| $I_{FSM}$   | 10 ms                                                       | $T_j = 25\text{ °C}$  | A    |
|             | sin 180°                                                    | $T_j = 150\text{ °C}$ | A    |
| $T_{jmax}$  |                                                             | 175                   | °C   |

### Electrical Characteristics

| Symbol     | Conditions                                        | min. | typ.  | max.  | Unit             |
|------------|---------------------------------------------------|------|-------|-------|------------------|
| $i^2t$     | $T_j = 150\text{ °C}$ , sin 180°, 10 ms           |      |       | 925   | A <sup>2</sup> s |
| $I_R$      | $T_j = 25\text{ °C}$ , $V_{RRM} = 1200\text{ V}$  |      |       | 0.12  | mA               |
|            | $T_j = 150\text{ °C}$ , $V_{RRM} = 1200\text{ V}$ |      | 7.00  | 14.00 | mA               |
| $V_F$      | $T_j = 25\text{ °C}$ , $I_F = 75\text{ A}$        |      | 2.17  | 2.49  | V                |
|            | $T_j = 150\text{ °C}$ , $I_F = 75\text{ A}$       |      | 2.11  | 2.42  | V                |
|            | $T_j = 175\text{ °C}$ , $I_F = 75\text{ A}$       |      | 1.96  | 2.27  | V                |
| $V_{(TO)}$ | $T_j = 150\text{ °C}$                             |      | 0.90  | 1.10  | V                |
| $r_T$      | $T_j = 150\text{ °C}$                             |      | 16.1  | 17.70 | mΩ               |
| $V_{(TO)}$ | $T_j = 175\text{ °C}$                             |      | 0.82  | 0.98  | V                |
| $r_T$      | $T_j = 175\text{ °C}$                             |      | 15.20 | 17.30 | mΩ               |

### Dynamic Characteristics

| Symbol    | Conditions                                     | min. | typ. | max. | Unit |
|-----------|------------------------------------------------|------|------|------|------|
| $t_{rr}$  | $T_j = 150\text{ °C}$ , 75 A, 600 V, 1500 A/μs |      | 0.5  |      | μs   |
| $E_{rr}$  | $T_j = 150\text{ °C}$ , 75 A, 600 V, 1500 A/μs |      | 4.2  |      | mJ   |
| $I_{rrm}$ | $T_j = 150\text{ °C}$ , 75 A, 600 V, 1500 A/μs |      | 58   |      | A    |

### Thermal Characteristics

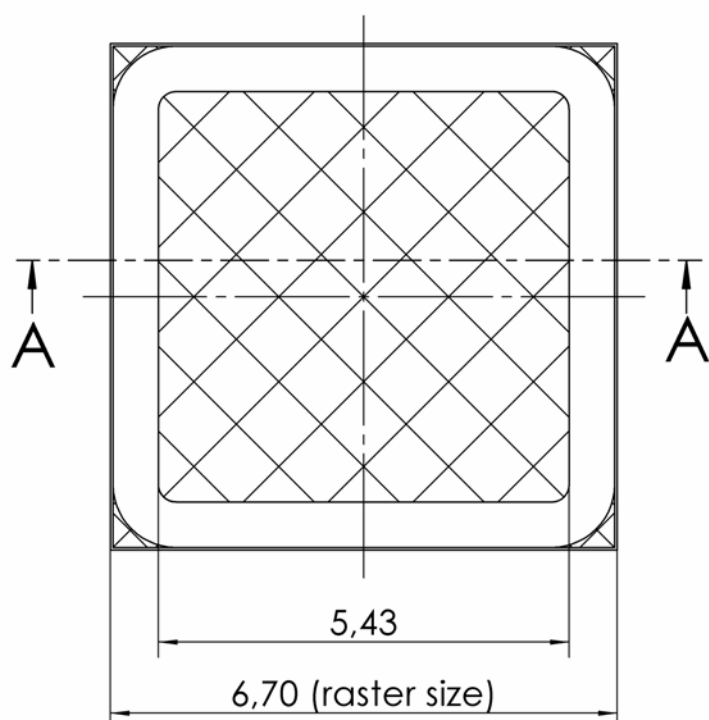
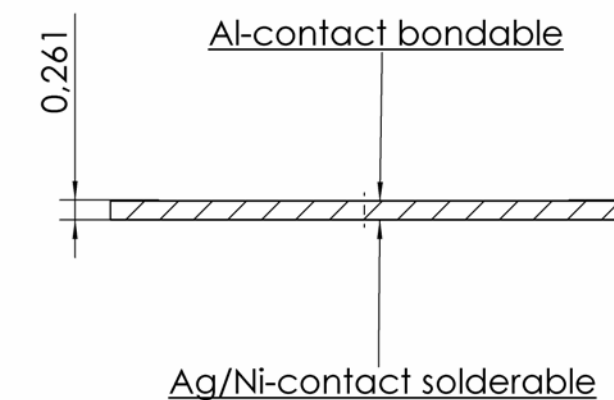
| Symbol        | Conditions         | min. | typ. | max. | Unit |
|---------------|--------------------|------|------|------|------|
| $T_j$         |                    | -40  |      | 175  | °C   |
| $T_{stg}$     |                    | -40  |      | 175  | °C   |
| $T_{solder}$  | 10 min.            |      |      | 250  | °C   |
| $T_{solder}$  | 5 min.             |      |      | 320  | °C   |
| $R_{th(j-c)}$ | Semitrans Assembly |      | 0.66 |      | K/W  |

### Mechanical Characteristics

| Symbol          | Conditions    | Values                     | Unit            |
|-----------------|---------------|----------------------------|-----------------|
| Raster size     |               | 6.70 x 6.70                | mm <sup>2</sup> |
| Area total      |               | 46                         | mm <sup>2</sup> |
| Anode           | Metallization | bondable (Al)              |                 |
| Cathode         | Metallization | solderable (Ag/Ni)         |                 |
| Wire bond       |               | Al, typ. diameter = 300 μm |                 |
| Package         |               | wafer frame                |                 |
| Chips / Package |               | 321                        | pcs             |



**SKCD**



die size after cutting  
□ 6,67 mm

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.